

# EARTH LEAKAGE CURRENT DETECTOR EARTH LEAKAGE CURRENT DETECTOR IC

## BD54123F

### General Description

BD54123F integrates leakage detector and amplifier. Especially, it is suitable for high sensitivity and a high-speed operation use, and since the operating temperature range is wide, it can be used for various uses.

### Key Specifications

- Operating supply voltage range : 12V to 22V
- Operating temperature range : -40°C to +85°C
- Supply current : 330 μA(typ.)
- Trip voltage : 4.92mV to 11.06mV
- Output current ability(Ta=-40°C) : -200 μA~(min.)

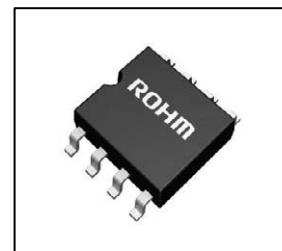
### Features

- Small temperature fluctuation and high input sensitivity
- Wide operating temperature range

### Packages

SOP8

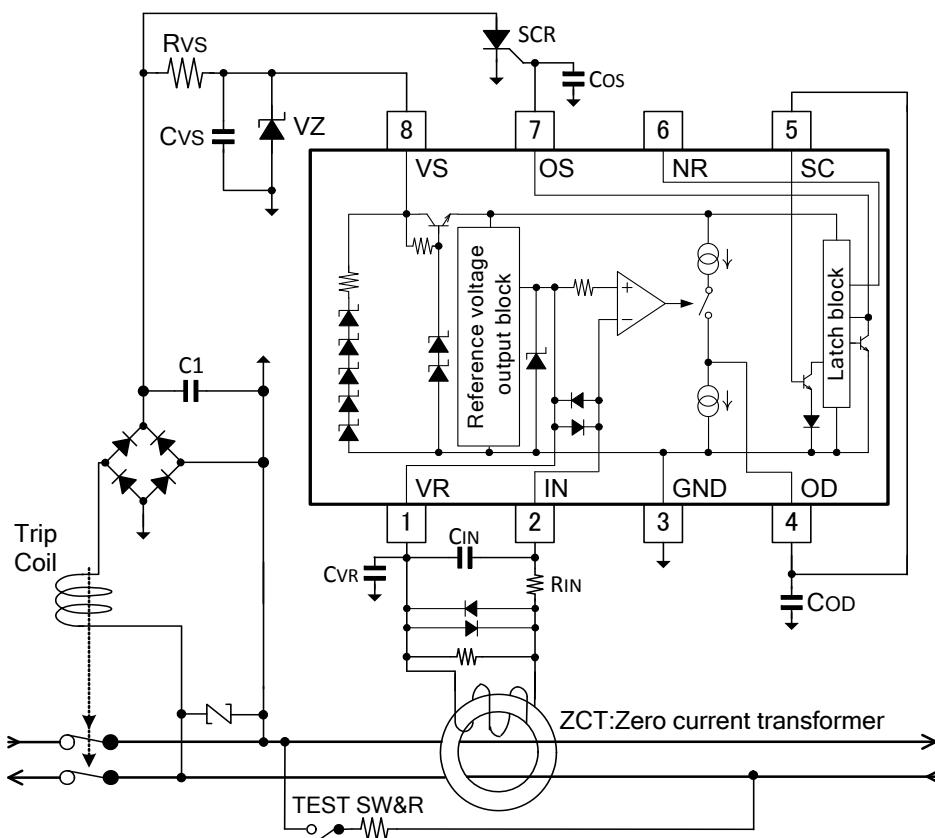
W(Typ.) x D(Typ.) x H(Max.)  
5.00mm x 6.20mm x 1.71mm



### Applications

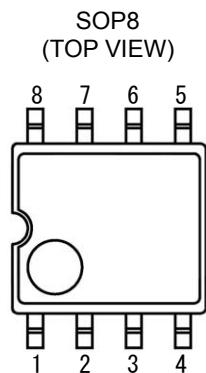
- Earth leakage circuit breaker
- Earth leakage circuit relay

### Typical Application Circuit Example

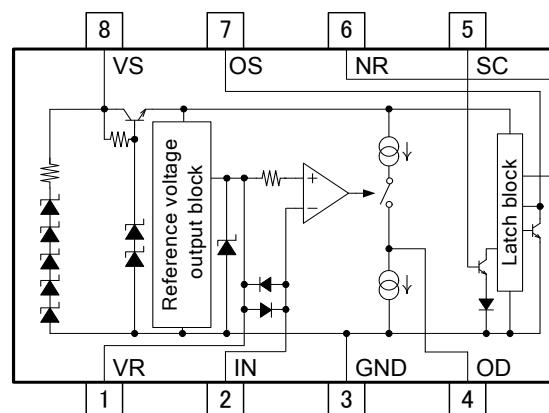


Product structure : Silicon monolithic integrated circuit    This product is not designed protection against radioactive rays.

### ●Pin Configurations



### ●Block Diagrams



### ●Pin Descriptions

Pin No.	Symbol	Function
1	VR	Reference voltage
2	IN	Input
3	GND	Ground
4	OD	Output of input comparator
5	SC	Input of latch circuit
6	NR	Noise absorption
7	OS	Output
8	VS	Power supply

### ●Absolute Maximum Ratings

(Ta=25°C)

Parameter	Symbol	Rating	Unit
Supply current *1	IS	8	mA
IN-VR current	I <sub>IN-VR</sub>	±250	mA
VR pin current	I <sub>VR</sub>	30	mA
IN terminal current	I <sub>IN</sub>	30	mA
SC terminal current	I <sub>SC</sub>	5	mA
Power Supply voltage	VS	36	V
Input terminal voltage	V <sub>VR/IN</sub>	17	V
OD/SC/NR/OS terminal voltage	V <sub>OD/SC/NR/OS</sub>	8	V
Power dissipation	P <sub>d</sub>	680 *2	mW
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\*1 The power-supply voltage is limited by the internal clamping circuit.

\*2 To use at temperature above Ta=25°C, reduce 5.5mW/°C. Mounted on a glass epoxy PCB (70mm×70mm×1.6mm)

### ● Recommended Operating Ratings

Parameter	Symbol	Limits	Unit
Supply voltage	VS	12 to 22	V
Operating temperature	T <sub>opr</sub>	-40 to +85	°C
External capacitor between VS and GND	C <sub>VS</sub>	1≤	μF
External capacitor between OS and GND	C <sub>OS</sub>	≤1	μF

### ● Electrical Characteristics

(Unless otherwise specified, VS=12V, GND=0V, Ta=25°C)

Parameter	Symbol	Temperature range	Limits			Unit	Conditions
			Min.	Typ.	Max.		
Supply current	IS1	-40°C	-	-	520	μA	$\Delta V_{IN}=V_{VR}-V_{IN}=30mV$
		25°C	-	330	500		
		85°C	-	-	460		
Trip voltage	V <sub>T</sub>	-40°C to +85°C	4.92	7.50	11.06	mV	$V_T=\Delta V_{IN}=V_{VR}-V_{IN}$
OD Source current	I <sub>ODSO</sub>	25°C	-27.2	-20.6	-14.0	μA	$\Delta V_{IN}=V_{VR}-V_{IN}=30mV$ , $V_{OD}=1.2V$
OD Sink current	I <sub>ODSI</sub>	25°C	16.7	26.0	35.3	μA	$V_{OD}=0.8V$ , $\Delta V_{IN}=V_{VR}-V_{IN}=0mV$
OS Source current	I <sub>OSO</sub>	-40°C	-200	-	-	μA	$V_{sc}=2.0V$ , $V_{os}=0.8V$
		25°C	-100	-	-		
		85°C	-75	-	-		
OS Sink current	I <sub>OSS</sub>	-40°C to +85°C	200	-	-	μA	$V_{sc}=0.2V$ , $V_{os}=0.2V$
SC ON voltage	V <sub>SCON</sub>	25°C	1.00	1.24	1.48	V	
Input clamp voltage	V <sub>IC</sub>	-40°C to +85°C	4.2	5.5	6.7	V	$I_{IC}=20mA$
Differential input clamp voltage	V <sub>IDC</sub>	-40°C to +85°C	0.6	1.0	1.4	V	$I_{IDC}=100mA$
Maximum current voltage	V <sub>SM</sub>	25°C	26	29	32	V	$IS=7mA$
Supply current 2 * <sup>1</sup>	I <sub>OS2</sub>	-40°C to +85°C	-100	-	-	μA	$IS=900\mu A$ , $V_{sc}=2.0V$ $V_{os}=0.8V$
Latch OFF Supply Voltage	V <sub>SOFF</sub>	25°C	0.5	-	-	V	
Operating time * <sup>2</sup>	t <sub>ON</sub>	25°C	1.8	2.9	4.0	ms	

\*1 Supply current 2 is OS source current value when the power supply current( $IS=900\mu A$ ) is given.

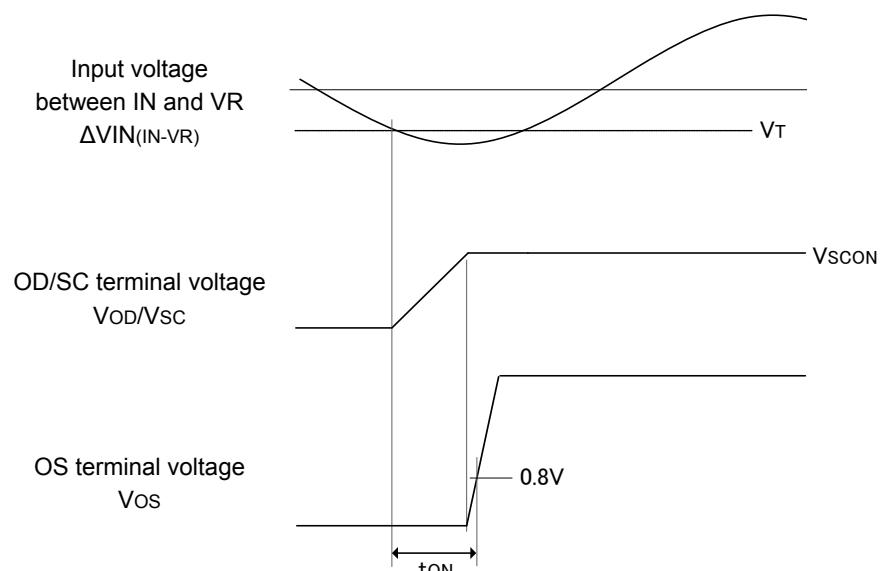
\*2 Operating time is time until output voltage reaches 0.8V after detecting the leakage signal.

Conditions : Capacitor(0.047μF) is connected between OD(OS) and GND.

### ● Test circuits

<b>1. IS1</b>	<b>2. VT</b>	<b>3. IODSO</b>
<b>4. IODSI</b>	<b>5. I OSSO / I OSSI</b>	<b>6. VSCON</b>
<b>7. VIC</b>	<b>8. VIDC</b>	<b>9. VSM</b>
<b>10. IOS2</b>	<b>11. VSOFF</b>	<b>12. tON</b>

### ● Timing Chart



●Typical Performance Curves(reference data)

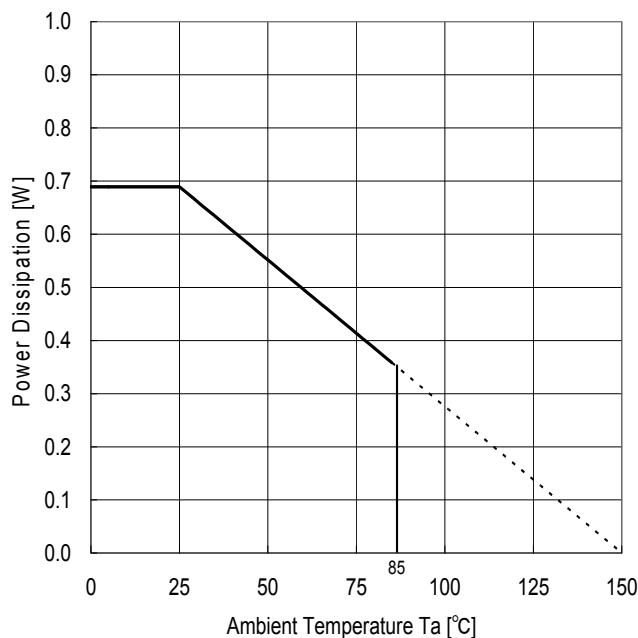


Figure 1  
Derating curve

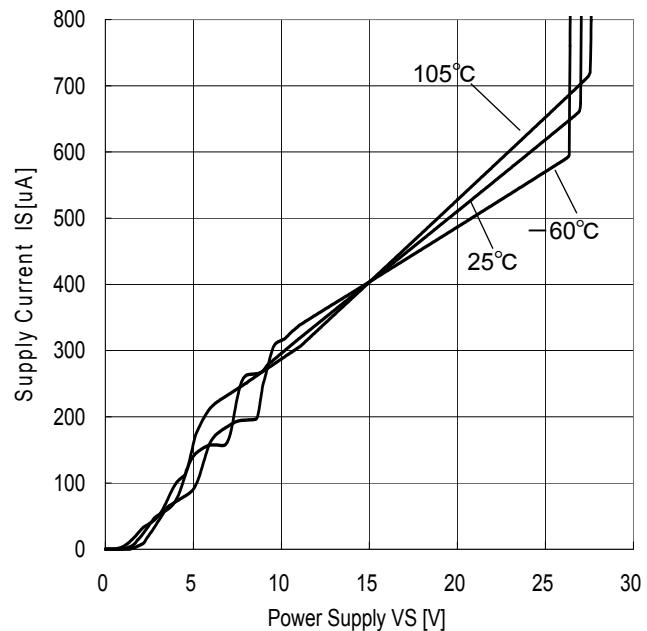


Figure 2  
Circuit current - Supply voltage

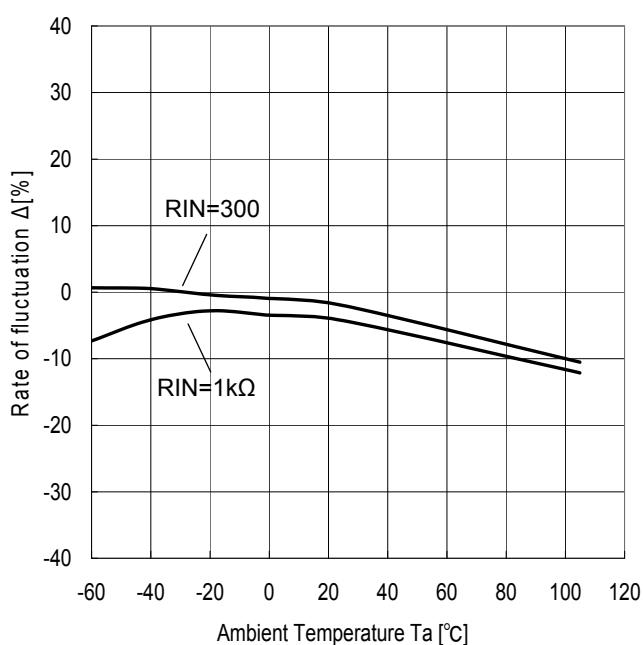


Figure 3  
Trip voltage fluctuation rate  
- Ambient temperature

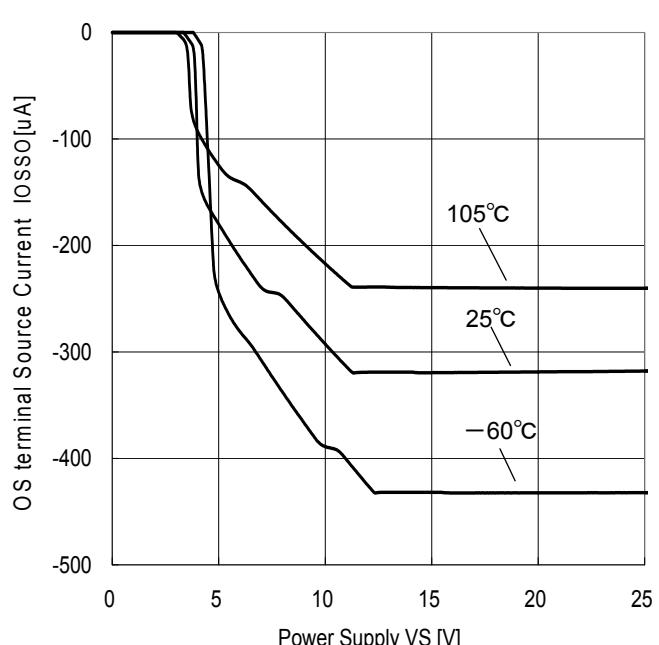


Figure 4  
OS terminal source current - Supply voltage

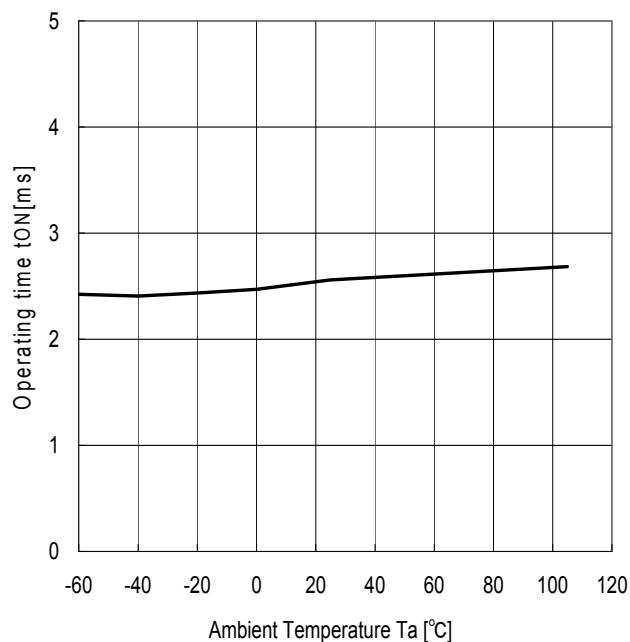


Figure 5  
Operating time - Ambient temperature

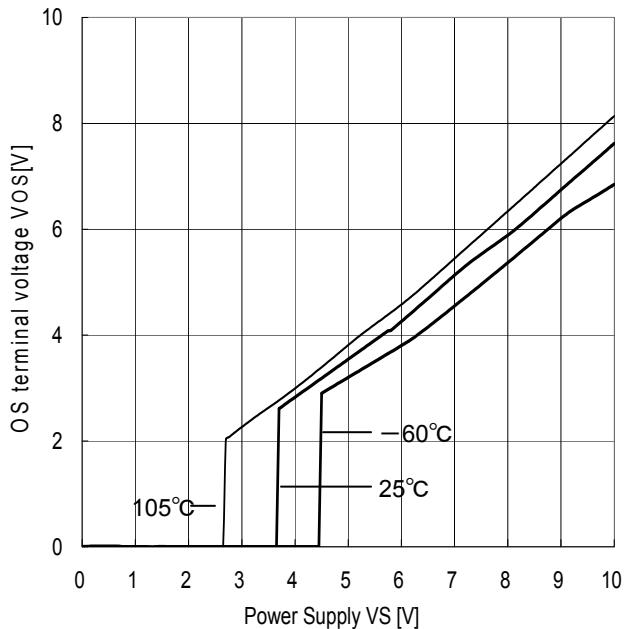


Figure 6  
Latch OFF supply voltage - Ambient temperature

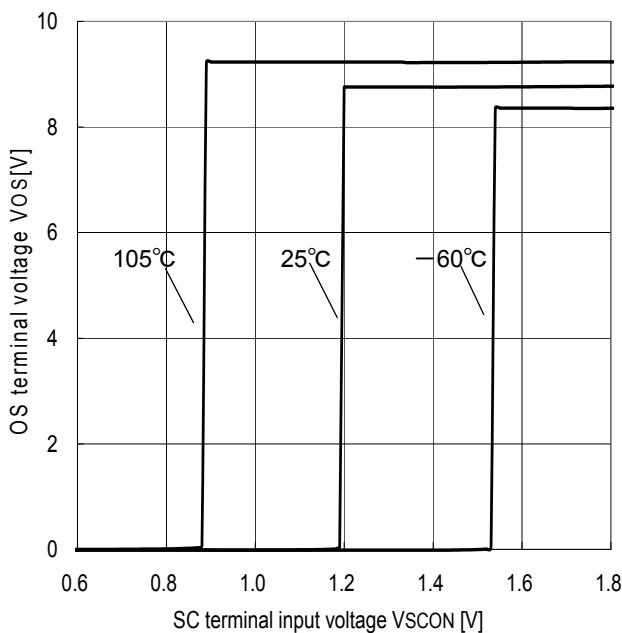


Figure 7  
SC ON voltage - Ambient temperature

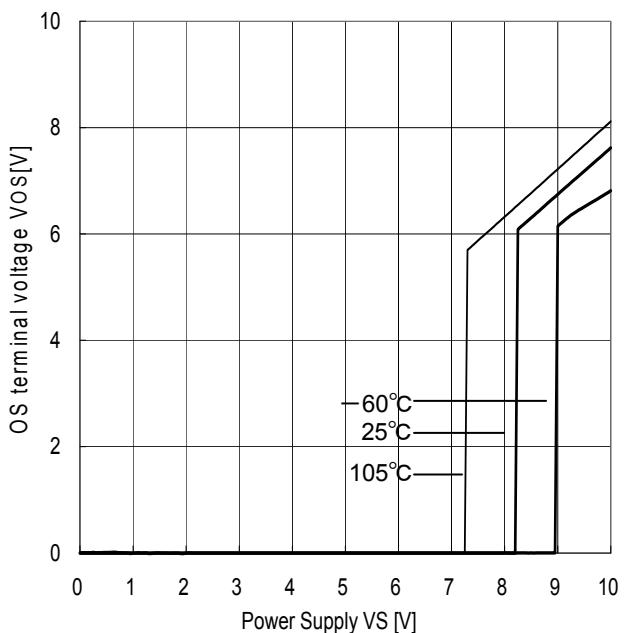


Figure 8  
Latch ON supply voltage - Ambient temperature

### ● Power Dissipation

Power dissipation(total loss) indicates the power that can be consumed by IC at  $T_a=25^{\circ}\text{C}$ (normal temperature).IC is heated when it consumed power, and the temperature of IC chip becomes higher than ambient temperature. The temperature that can be accepted by IC chip depends on circuit configuration, manufacturing process, and consumable power is limited. Power dissipation is determined by the temperature allowed in IC chip (maximum junction temperature) and thermal resistance of package (heat dissipation capability). The maximum junction temperature is typically equal to the maximum value in the storage temperature range. Heat generated by consumed power of IC radiates from the mold resin or lead frame of the package. The parameter which indicates this heat dissipation capability(hardness of heat release)is called thermal resistance, represented by the symbol  $\theta_{ja}^{\circ}\text{C}/\text{W}$ .The temperature of IC inside the package can be estimated by this thermal resistance. Fig.9(a) shows the model of thermal resistance of the package. Thermal resistance  $\theta_{ja}$ , ambient temperature  $T_a$ , junction temperature  $T_j$ , and power dissipation  $P_d$  can be calculated by the equation below

$$\theta_{ja} = (T_j - T_a) / P_d \quad ^{\circ}\text{C}/\text{W} \quad \dots \dots \quad (I)$$

Derating curve in Fig.9(b) indicates power that can be consumed by IC with reference to ambient temperature. Power that can be consumed by IC begins to attenuate at certain ambient temperature. This gradient is determined by thermal resistance  $\theta_{ja}$ . Thermal resistance  $\theta_{ja}$  depends on chip size, power consumption, package, ambient temperature, package condition, wind velocity, etc even when the same of package is used. Thermal reduction curve indicates a reference value measured at a specified condition. Fig.10(a) show a derating curve for an example of BD54123F.

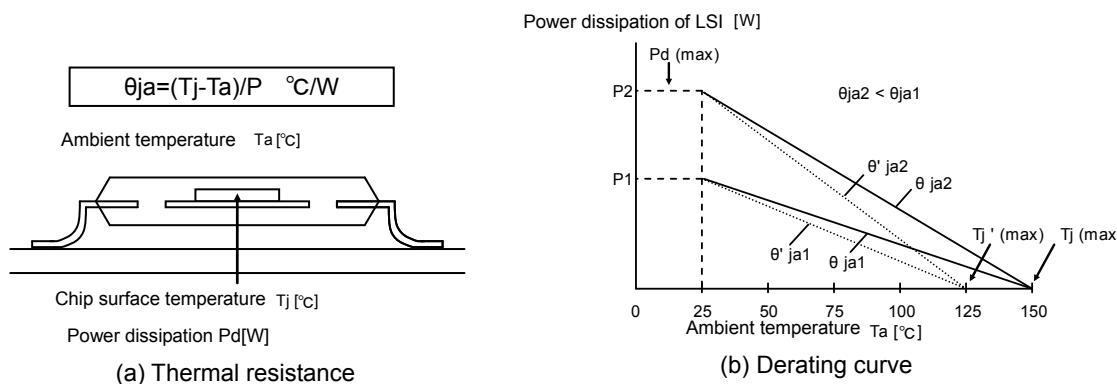
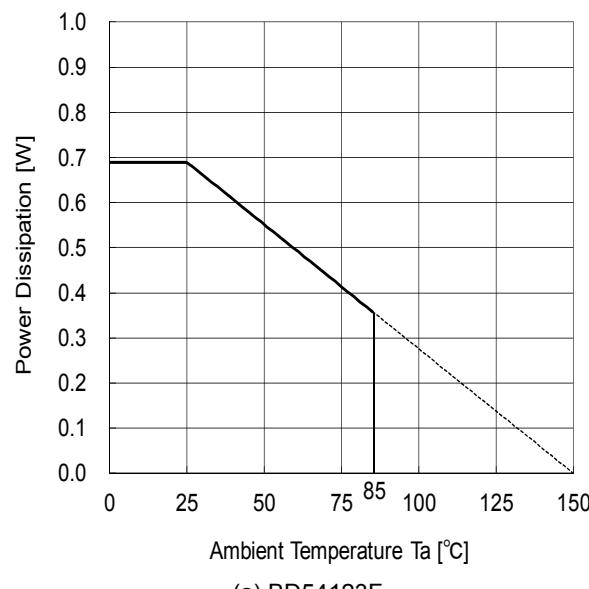


Figure 9. Thermal resistance and derating



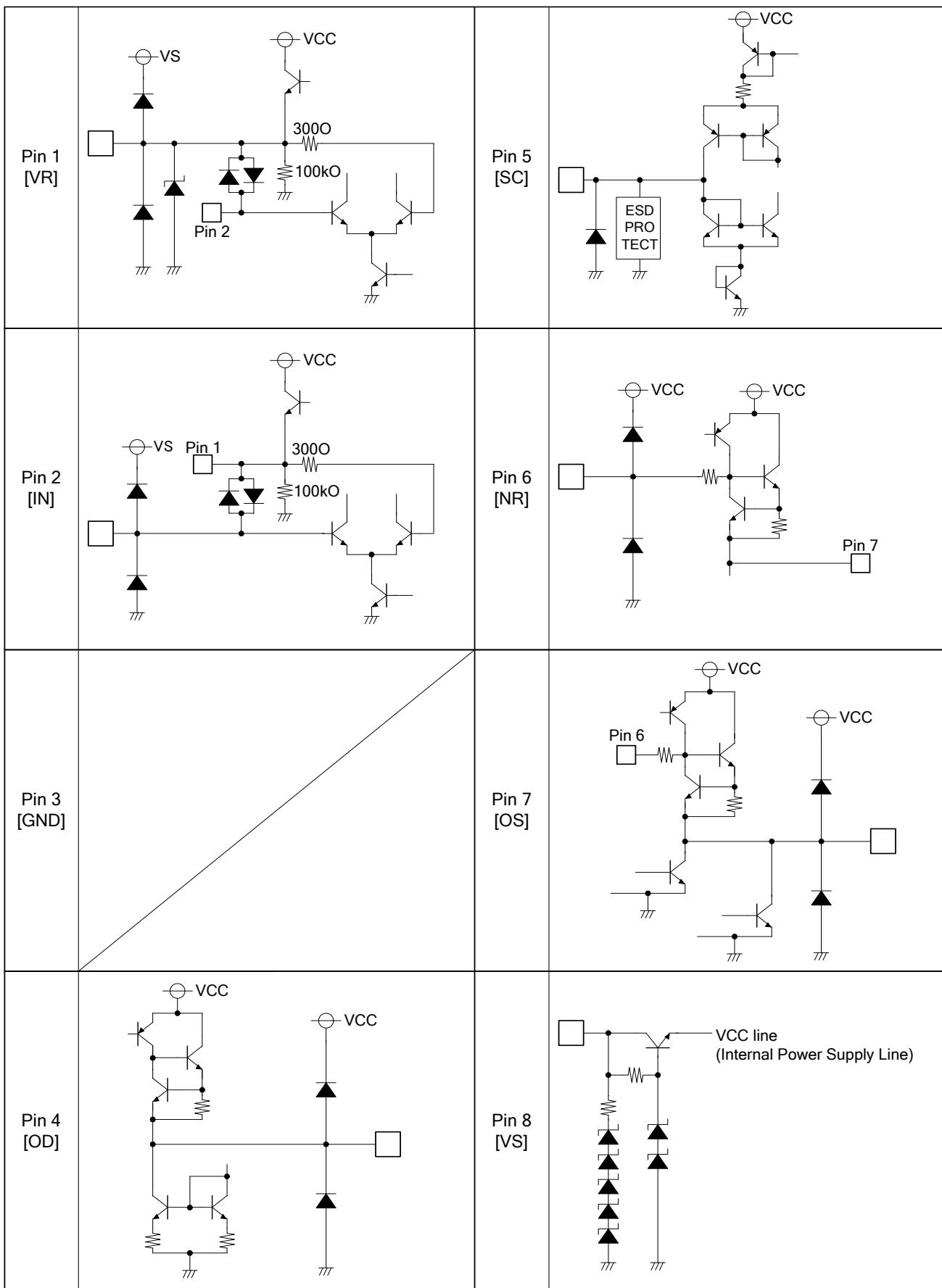
	Derating curve slope	UNIT
BD54123F	5.5	mW/°C

When using the unit above  $T_a=25^{\circ}\text{C}$ , subtract the value above per degree°C

Permissible dissipation is a value when FR4 glass epoxy board 70mm×70mm×1.6mm (cooper foil area below 3%) is mounted.

Figure 10. Derating curve

## ● I/O equivalence circuit



**●Operational Notes****1) Absolute maximum ratings**

Absolute maximum ratings are the values which indicate the limits, within which the given voltage range can be safely charged to the terminal. However, it does not guarantee the circuit operation.

**2) Power dissipation Pd**

Using the unit in excess of the rated power dissipation may cause deterioration in electrical characteristics due to a rise in chip temperature, including reduced current capability. Therefore, please take into consideration the power dissipation (Pd) under actual operating conditions and apply a sufficient margin in thermal design. Refer to the thermal derating curves for more information.

**3) Terminal short-circuits**

When the output and power supply terminals are shorted, excessive output current may flow, resulting in undue heat generation and, subsequently, destruction.

**4) Ground terminal voltage**

All time, Ground terminal voltage should keep lowest voltage.

In addition, please confirm whether there is not really a terminal becoming the voltage that is lower than GND including a transitional phenomenon.

**5) Operation in a strong electromagnetic field**

Operation in a strong electromagnetic field may cause malfunctions.

**6) Short-circuit between pins and erroneous mounting**

Incorrect mounting may damage the IC. In addition, the presence of foreign particles between the outputs, the output and the power supply, or the output and GND may result in IC destruction.

**7) IC handling**

Applying mechanical stress to the IC by deflecting or bending the board may cause fluctuations in the electrical characteristics due to piezo resistance effects.

**8) Board inspection**

Connecting a capacitor to a pin with low impedance may stress the IC. Therefore, discharging the capacitor after every process is recommended. In addition, when attaching and detaching the jig during the inspection phase, ensure that the power is turned off before inspection and removal. Furthermore, please take measures against ESD in the assembly process as well as during transportation and storage.

**Status of this document**

The Japanese version of this document is formal specification. A customer may use this translation version only for a reference to help reading the formal version.

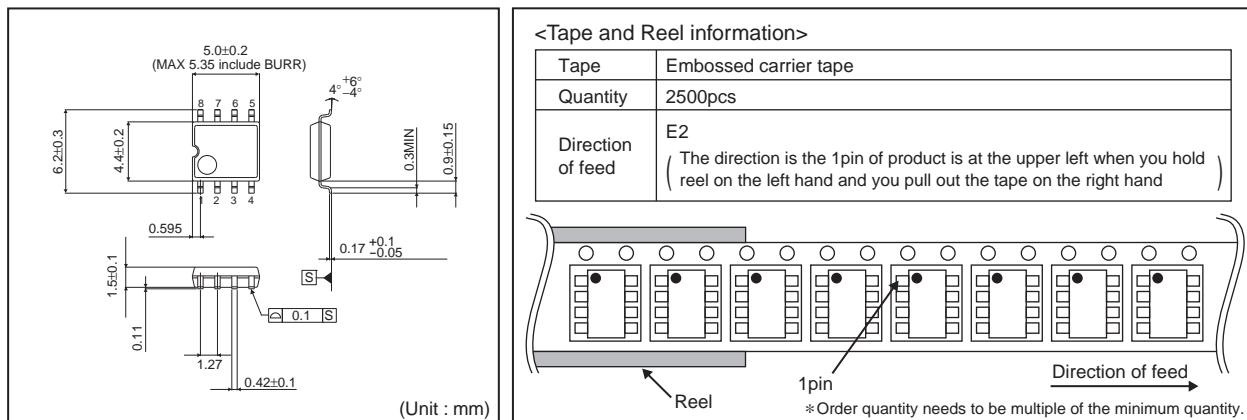
If there are any differences in translation version of this document formal version takes priority.

### ● Ordering Information

B	D	5	4	1	2	3	F	E 2
Part Number					Package F: SOP8			
					Packaging and forming specification E2: Embossed tape and reel (SOP8)			

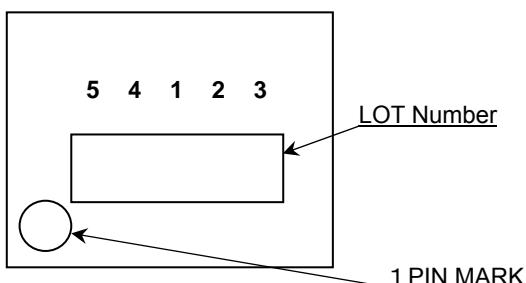
### ● Physical Dimension Tape and Reel Information

#### SOP8



### ● Marking Diagrams

SOP8  
(TOP VIEW)



**●Revision History**

Date	Revision	Changes
2012.10.29	001	New Release